

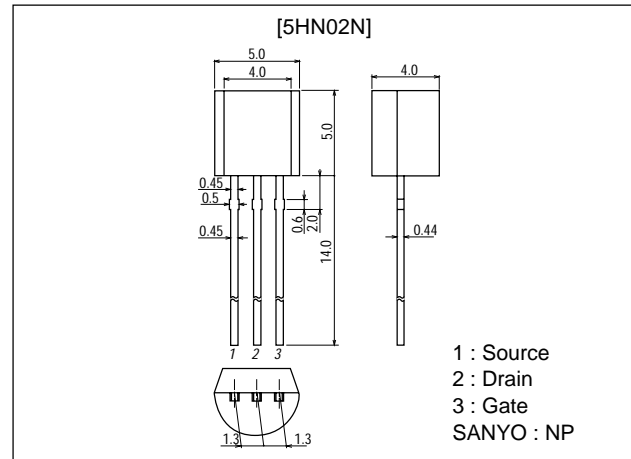
**5HN02N****Ultrahigh-Speed Switching Applications****Features**

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

Package Dimensions

unit:mm

2178

**Specifications****Absolute Maximum Ratings** at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		50	V
Gate-to-Source Voltage	V_{GSS}		± 20	V
Drain Current (DC)	I_D		0.2	A
Drain Current (pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	0.8	A
Allowable Power Dissipation	P_D		0.4	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1\text{mA}$, $V_{GS}=0$	50			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=50\text{V}$, $V_{GS}=0$			10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16\text{V}$, $V_{DS}=0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}$, $I_D=100\mu\text{A}$	1		2.4	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10\text{V}$, $I_D=100\text{mA}$	0.22	0.31		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=100\text{mA}$, $V_{GS}=10\text{V}$		1.8	2.3	Ω
	$R_{DS(on)2}$	$I_D=50\text{mA}$, $V_{GS}=4\text{V}$		2.3	3.2	Ω

Marking : YF

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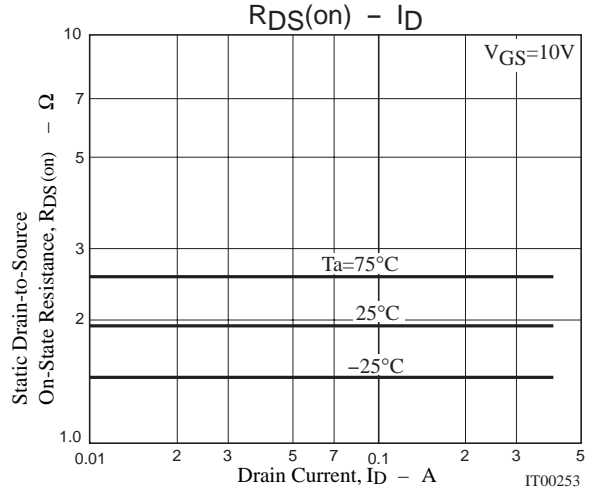
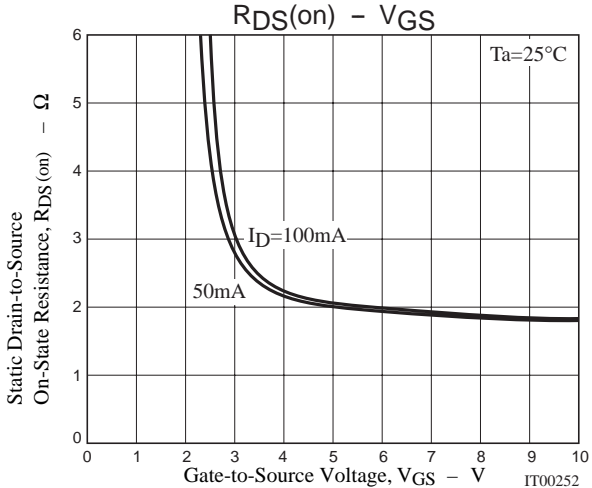
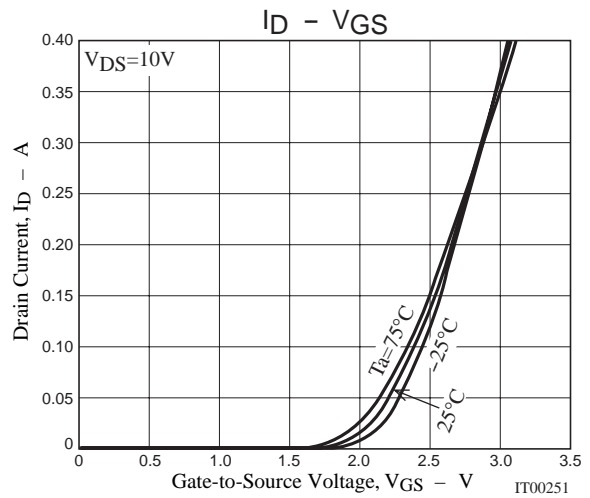
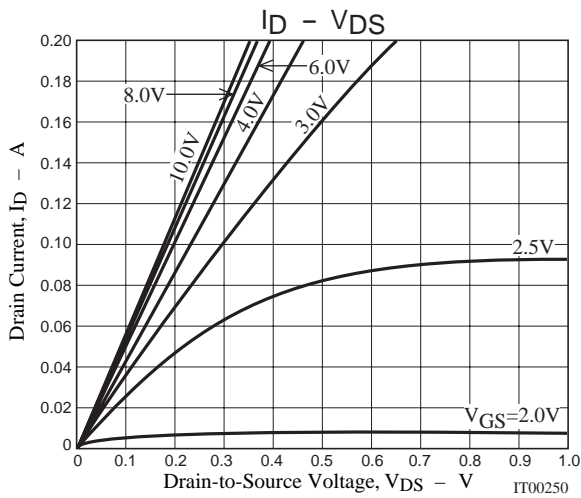
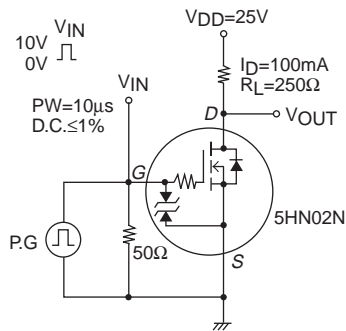
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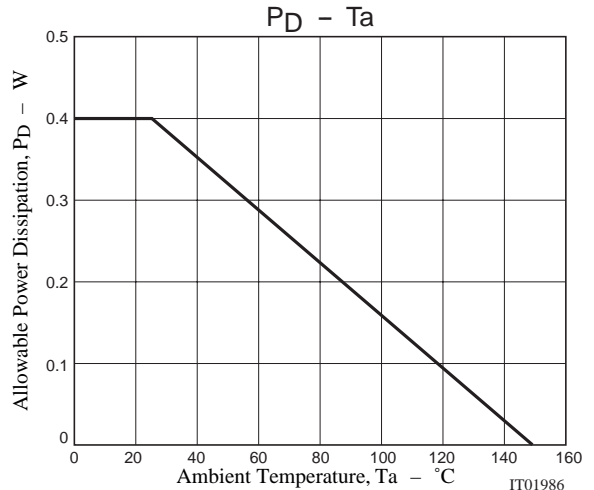
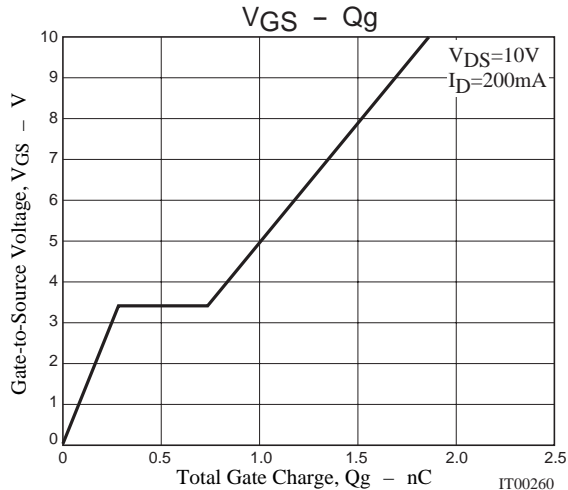
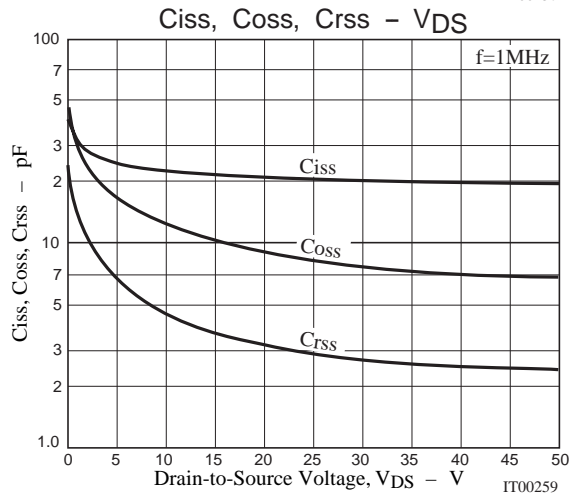
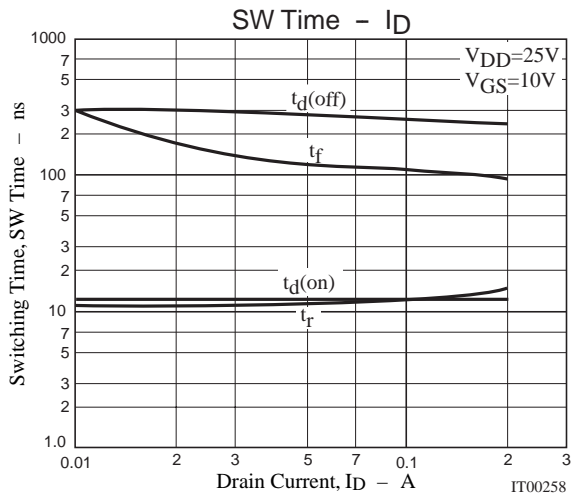
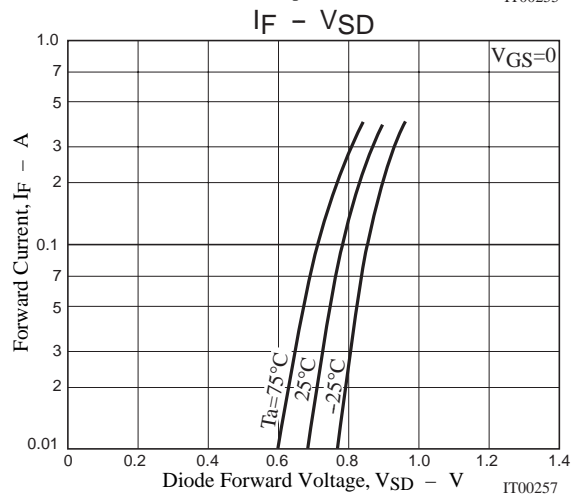
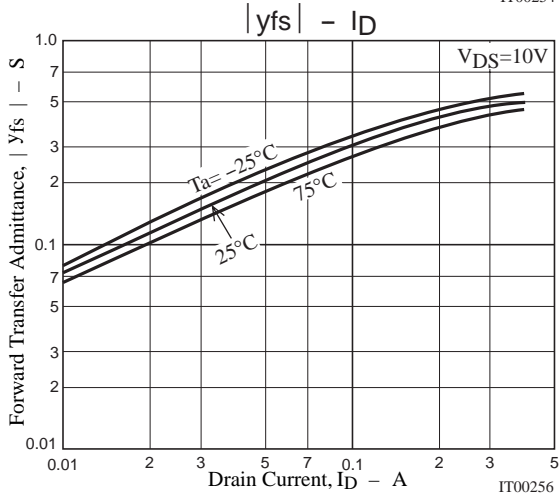
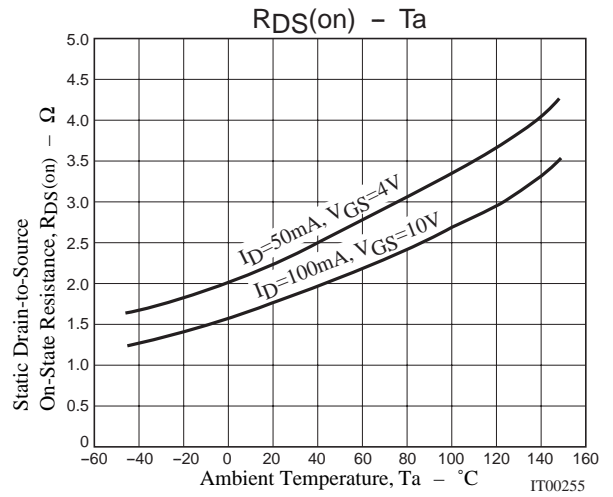
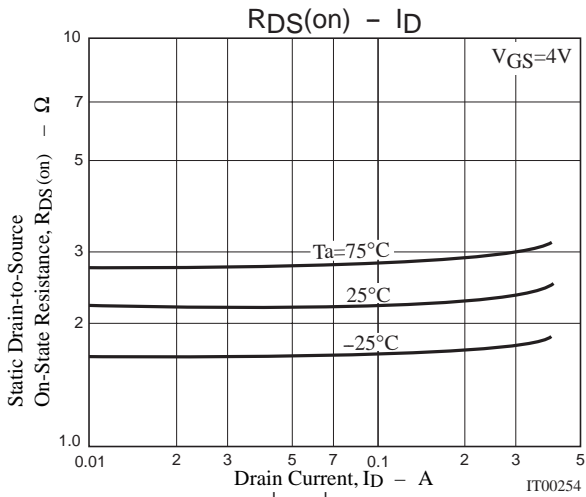
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	$V_{DS}=10V, f=1MHz$		22		pF
Output Capacitance	Coss	$V_{DS}=10V, f=1MHz$		12		pF
Reverse Transfer Capacitance	Crss	$V_{DS}=10V, f=1MHz$		4.6		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		12		ns
Rise Time	t_r	See specified Test Circuit		12		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		260		ns
Fall Time	t_f	See specified Test Circuit		110		ns
Total Gate Charge	Qg	$V_{DS}=10V, V_{GS}=10V, I_D=200mA$		1.86		nC
Gate-to-Source Charge	Qgs	$V_{DS}=10V, V_{GS}=10V, I_D=200mA$		0.28		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=10V, V_{GS}=10V, I_D=200mA$		0.45		nC
Diode Forward Voltage	V_{SD}	$I_S=200mA, V_{GS}=0$		0.83	1.2	V

Switching Time Test Circuit



5HN02N



Note on usage : Since the 5HN02N is designed for high-speed switching applications, please avoid using this device in the vicinity of highly charged objects.

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